Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020M-6 (SOT1220-2) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Logic-level compatible
- · Very fast switching
- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- · Exposed drain pad for excellent thermal conduction

3. Applications

- Charging switch for portable devices
- DC-to-DC converters
- · Power management in battery-driven portable devices
- · Computing power management

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-30	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	$V_{GS} = -10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-12.3	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -8.7 A; T_j = 25 °C		-	12.7	15.5	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



30 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 1 7 7 1 6	D
2	D	drain		
3	G	gate	2 5	G (FY)
4	S	source	3 8 4	s
5	D	drain	Transparent top view	017aaa094
6	D	drain	DFN2020M-6 (SOT1220-2)	
7	D	drain		
8	S	source	1	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB12R7EP	DFN2020M-6	plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals; body 2 x 2 x 0.65 mm	SOT1220-2			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB12R7EP	ZM

30 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-12.3	Α
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-8.7	Α
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-5.5	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-35	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.8	W
		T _{amb} = 25 °C	[1]	-	1.9	W
		T _{sp} = 25 °C		-	12.5	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode			'		,
Is	source current	T _{amb} = 25 °C	[1]	-	-1.8	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

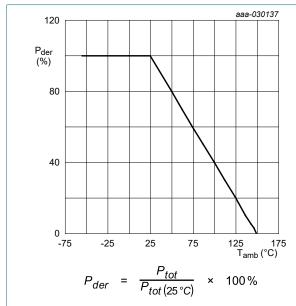


Fig. 1. Normalized total power dissipation as a function of ambient temperature

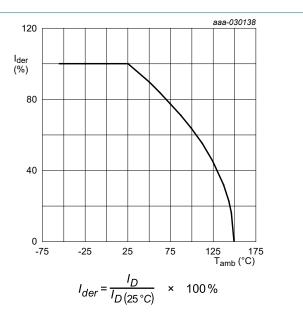


Fig. 2. Normalized continous drain current as a function of ambient temperature

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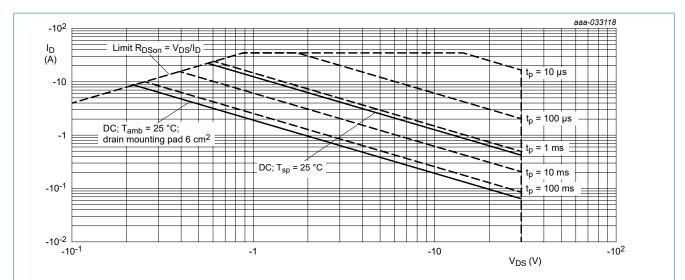


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

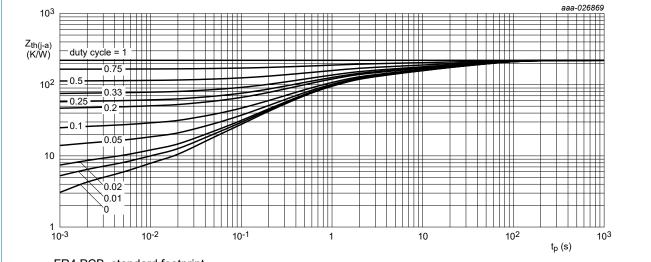
30 V, P-channel Trench MOSFET

9. Thermal characteristics

Table 6. Thermal characteristics

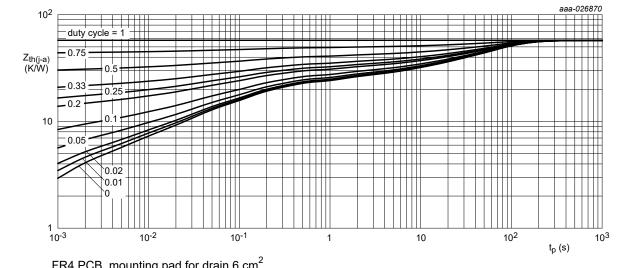
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance from	in free air	[1]	-	223	256	K/W
	junction to ambient		[2]	-	57	66	K/W
		in free air; t ≤ 5 s	[2]	-	29	33	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	6	10	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 4.



FR4 PCB, mounting pad for drain 6 cm²

Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-1	-1.5	-2.5	V
I _{DSS}	drain leakage current	V _{DS} = -30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = -10 \text{ V}; I_D = -8.7 \text{ A}; T_j = 25 \text{ °C}$	-	12.7	15.5	mΩ
	resistance	V_{GS} = -10 V; I_D = -8.7 A; T_j = 150 °C	-	20	25	mΩ
		V_{GS} = -4.5 V; I_D = -7 A; T_j = 25 °C	-	16	24	mΩ
9 _{fs}	forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -8.6 \text{ A}; T_j = 25 \text{ °C}$	-	18	-	S
R_G	gate resistance	f = 1 MHz	-	7.9	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -15 V; I_{D} = -8.6 A; V_{GS} = -10 V;	-	33	49	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	4	-	nC
Q _{GD}	gate-drain charge		-	6.6	-	nC
C _{iss}	input capacitance	V _{DS} = -15 V; f = 1 MHz; V _{GS} = 0 V;	-	1638	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	191	-	pF
C _{rss}	reverse transfer capacitance	_	-	164	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -15 \text{ V}; I_D = -8.6 \text{ A}; V_{GS} = -10 \text{ V};$	-	3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	67	-	ns
t _f	fall time		-	27	-	ns
Source-drai	n diode					
V_{SD}	source-drain voltage	I _S = -1.8 A; V _{GS} = 0 V; T _j = 25 °C	-	-0.8	-1.2	V
		-			•	

30 V, P-channel Trench MOSFET

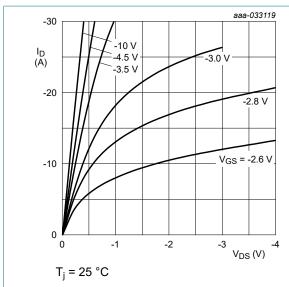


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

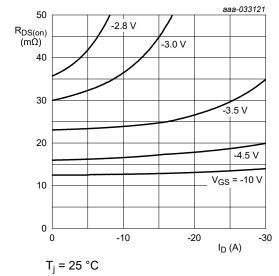


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

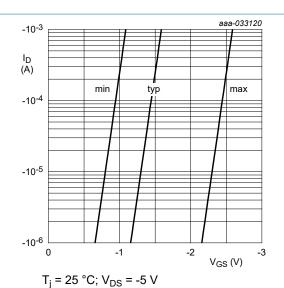


Fig. 7. Subthreshold drain current as a function of gate-source voltage

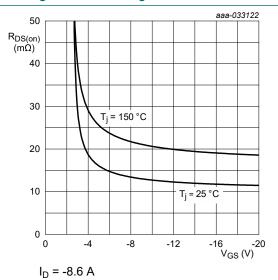


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

30 V, P-channel Trench MOSFET

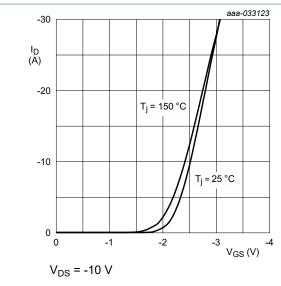


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

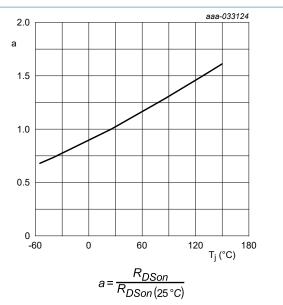


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

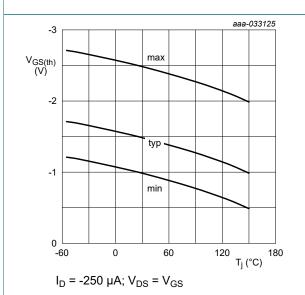
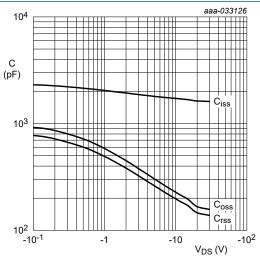


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

30 V, P-channel Trench MOSFET

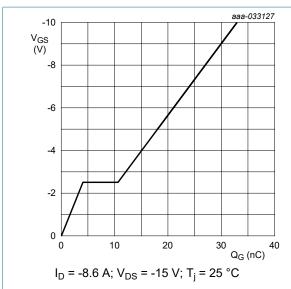


Fig. 14. Gate-source voltage as a function of gate charge; typical values

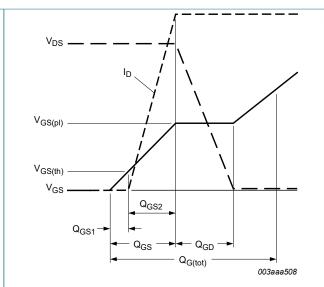


Fig. 15. Gate charge waveform definitions

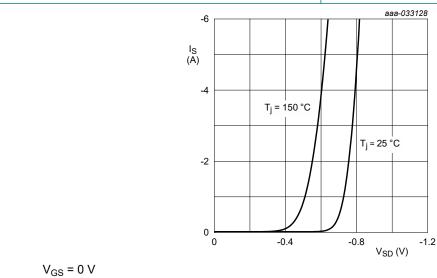
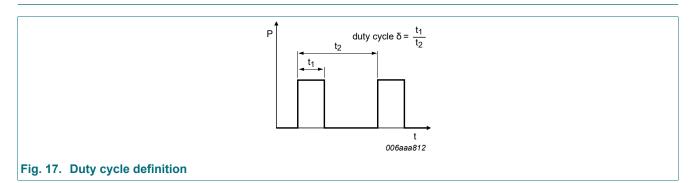


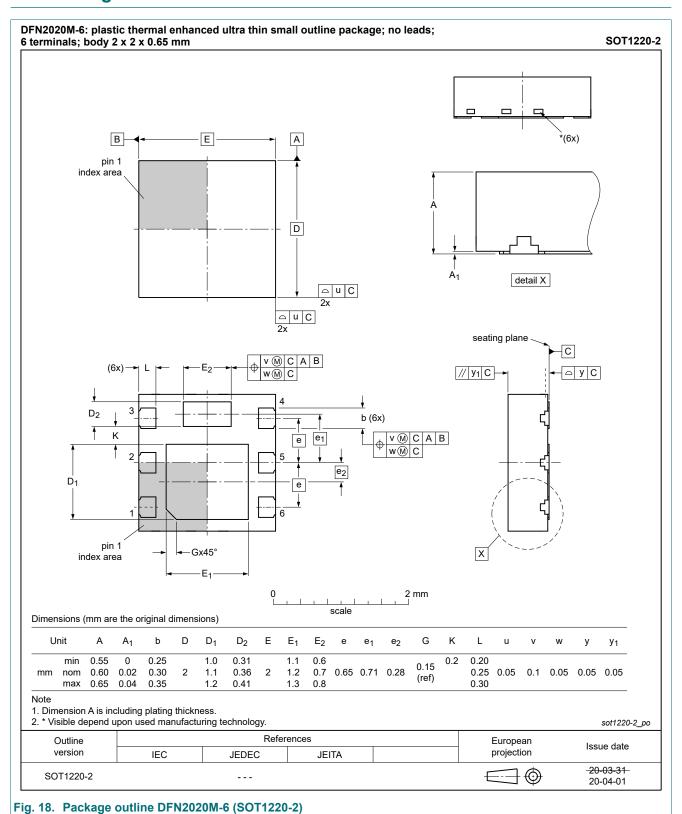
Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information



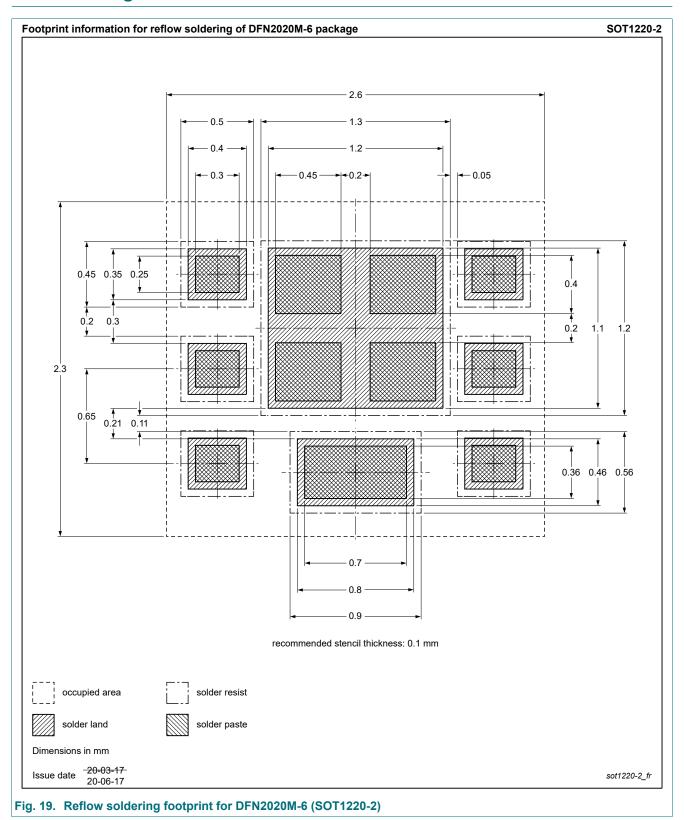
30 V, P-channel Trench MOSFET

12. Package outline



30 V, P-channel Trench MOSFET

13. Soldering



30 V, P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB12R7EP v.1	20210218	Product data sheet	-	-

30 V, P-channel Trench MOSFET

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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30 V, P-channel Trench MOSFET

Contents

General description	1
Features and benefits	1
Applications	1
Quick reference data	1
Pinning information	2
Ordering information	2
Marking	2
Limiting values	3
Thermal characteristics	5
Characteristics	6
Test information	9
Package outline	10
Soldering	11
Revision history	12
Legal information	
	Features and benefits

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